

Form PTO-1449		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. D/A2535		APPLICATION NO. 10/607860	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT Beng S. Ong et al.			
				FILING DATE		GROUP ART UNIT	
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE	CLASS	SUB CLASS		
TTN	6,387,727 B1	5/14/2002	Katz et al.	438	99		
TTN	2002/0164835 A1	11/7/2002	Dimitrakopoulos et al.	439	99		
TTN	4,587,189	5/6/1986	Hor et al.	430	59		
TTN	5,225,307	7/6/1993	Hor et al.	430	136		

FOREIGN PATENT DOCUMENTS

	COUNTRY	DOCUMENT NUMBER	PUBLICATION DATE	NAME OF PATENTEE OR APPLICANT	TRANSLATION Y/N

OTHER DOCUMENTS (Including Author (in CAPS), Title, Publication Date, Pages, etc.)

TTN	Amit Babel et al., "Electron Transport in Thin-Film Transistors from an n-Type Conjugated Polymer," <i>Adv. Mater.</i> 14, No. 5, pp. 371-374 (March 4, 2002)
TTN	H.E. Katz et al., "A soluble and air-stable organic semiconductor with high electron mobility," <i>Nature</i> , Vol. 404, pp. 478-480 (March 30, 2000).
TTN	Patrick R. L. Malenfant et al., "N-type organic thin-film transistor with high field-effect mobility based on a N,N'-dialkyl-3,4,9,10-perylene tetracarboxylic diimide derivative," <i>Applied Physics Letters</i> , Vol. 80, No. 14, pp. 2517-2519 (April 8, 2002).
TTN	Howard E. Katz et al., "Naphthalenetetracarboxylic Diimide-Based n-Channel Transistor Semiconductors: Structural Variation and Thiol-Enhanced Gold Contacts," <i>J. Am. Chem. Soc.</i> , Vol. 122, pp. 7787-7792 (2000).
TTN	J. H. Schon et al., "Perylene: A promising organic field-effect transistor material," <i>Applied Physics Letters</i> , Vol. 77, No. 23, pp. 3776-3778 (December 4, 2000).
EXAMINER	DATE CONSIDERED 10/18/04.
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	